

COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES
- COMPLEMENTARY PNP NPN DEVICES

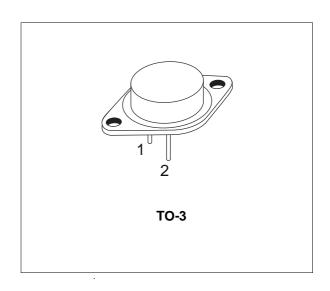
APPLICATION

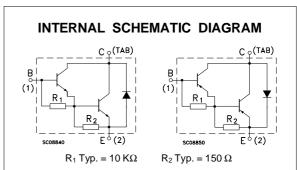
- AUDIO POWER AMPLIFIER
- DC-AC CONVERTER
- EASY DRIVER FOR LOW VOLTAGE DC MOTOR
- GENERAL POWER SWITCHING

DESCRIPTION

The MJ2501 is a Silicon Epitaxial-Base PNP power transistors in monolithic Darlington configuration, mounted in Jedec TO-3 metal case. It is intented for use in power linear and switching applications.

The complementary NPN type is the MJ3001.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit	
		PNP	MJ2501		
		NPN	MJ3001		
V _{CBO}	Collector-base Voltage (I _E = 0)		80	V	
V_{CEO}	Collector-emitter Voltage (I _B = 0)		80	V	
V _{EBO}	Emitter-base Voltage (I _C = 0)		5		
Ic	Collector Current		10		
lΒ	Base Current		0.2		
P _{tot}	Total Dissipation at T _c ≤ 25 °C		150	W	
T _{stg}	Storage Temperature		-65 to 200	°C	
Tj	Max. Operating Junction Temperature		200	°C	

For PNP types voltage and current values are negative.

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THERMAL DATA

R _{thj-case} Thermal Resistance Junction-case	Max	1.17	°C/W
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

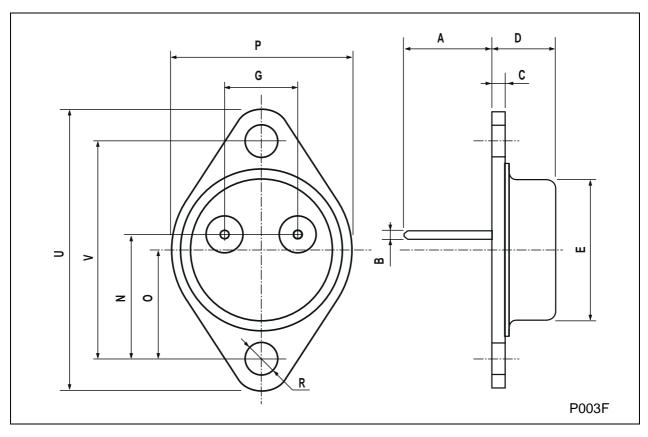
Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
ICER	Collector Cut-off Current ($R_{BE} = 1 K\Omega$)	V _{CE} = 80 V T _{case} = 150 °C V _{CF} = 80 V				1	mA mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 30 V V _{CE} = 40 V				1 1	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V				2	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA		80			V
V _{CE(sat)} *	Collector-emitter Saturation Voltage	I _C = 5 A I _C = 10 A	I _B = 20 mA I _B = 50 mA			2 4	V V
V _{BE} *	Base-emitter Voltage	I _C = 5 A	V _{CE} = 3 V			3	V
h _{FE} *	DC Current Gain	I _C = 5 A	V _{CE} = 3 V	1000			

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^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 % For PNP types voltage and current values are negative.

TO-3 MECHANICAL DATA

DIM.	mm			inch			
-	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α	11.00		13.10	0.433		0.516	
В	0.97		1.15	0.038		0.045	
С	1.50		1.65	0.059		0.065	
D	8.32		8.92	0.327		0.351	
E	19.00		20.00	0.748		0.787	
G	10.70		11.10	0.421		0.437	
N	16.50		17.20	0.649		0.677	
Р	25.00		26.00	0.984		1.023	
R	4.00		4.09	0.157		0.161	
U	38.50		39.30	1.515		1.547	
V	30.00		30.30	1.187		1.193	



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